L Number	Hits	Search Text	DB	Time stamp
-	111	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:00
		switch\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	6	5895936.URPN.	USPAT	2004/10/29 08:54
_	9	("5003356" "5032883" "5313066" "5319206"	USPAT	2004/10/29 08:54
		"5352897" "5396072" "5463225" "5498880"	001711	2001, 20, 25 0015 1
		"5563421").PN.		
	110	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 09:39
-	118	switch\$3) and (memory capacitor) and ohmic	US-PGPUB;	2004/10/23 03.33
		Switch\$3) and (memory capacitor) and online		
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/40/20 00 40
-	111	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 09:40
		switch\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	80	((thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 09:40
		switch\$3) and (memory capacitor) and ohmic) not ((thin adj	US-PGPUB;	
		film adj transistor\$1 tft) with (sensor\$3 and switch\$3) same	EPO; JPO;	
		capacitor)	DERWENT;	
i			IBM_TDB	
-	3	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:01
		access\$3) same capacitor	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	3	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:01
		acces\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	4	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:44
	•	access\$3) and capacitor not ((thin adj film adj transistor\$1	US-PGPUB;	
1		tft) with (sensor\$3 and access\$3) same capacitor)	EPO; JPO;	
		The state of the s	DERWENT;	
			IBM_TDB	
_	2	("5466620").PN.	USPAT;	2004/10/29 11:50
	_	,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("5436182").PN.	USPAT;	2004/10/29 11:50
		(5.55252 / 11.11	US-PGPUB;	
]			EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
_	4236	(257/59,53,54,57,184,187).CCLS.	USPAT;	2004/10/29 13:38
1 -	7230	(23/133/33/37/37/10/1/10///	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1910	(tff thin near film near transistor) and	USPAT;	2004/10/29 13:38
_	1819	(tft thin near film near transistor) and	US-PGPUB;	2007/10/23 13:30
		((257/59,53,54,57,184,187).CCLS.)		
			EPO; JPO;	[·
			DERWENT;	
I	1	I	IBM_TDB	1

-	821	((tft thin near film near transistor) and	USPAT;	2004/10/29 13:38
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	US-PGPUB;	
		memory)	EPO; JPO;	
,		,	DERWENT;	
			IBM_TDB	
-	587	(tft thin near film near transistor) same switch\$3 and (((tft	USPAT;	2004/10/29 13:39
		thin near film near transistor) and	US-PGPUB;	
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
		memory))	DERWENT;	
			IBM_TDB	
-	571	(tft thin near film near transistor) with switch\$3 and (((tft	USPAT;	2004/10/29 13:39
		thin near film near transistor) and	US-PGPUB;	
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
		memory))	DERWENT;	
			IBM_TDB	
-	511	(tft thin near film near transistor) near3 switch\$3 and (((tft	USPAT;	2004/10/29 13:47
		thin near film near transistor) and	US-PGPUB;	
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
		memory))	DERWENT;	
			IBM_TDB	
-	24	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/10/29 14:19
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	US-PGPUB;	,
		memory)) and dual near3 electrode	EPO; JPO;	4
			DERWENT;	
			IBM_TDB	
-	16	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:24
		memory) and ((257/59,53,54,57,184,187).CCLS.))) and	US-PGPUB;	
		dual near3 electrode	EPO; JPO;	
*	ļ	,	DERWENT;	
	1		IBM_TDB	2004/40/20 44-20
-	31	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:30
		memory) and (438/\$6 257/\$6))) and dual near3 electrode	US-PGPUB;	
		not ((((tft thin near film near transistor) same (capacitor	EPO; JPO;	
	1	memory) and ((257/59,53,54,57,184,187).CCLS.))) and	DERWENT;	
		dual near3 electrode)	IBM_TDB	2004/10/20 14/24
-	52	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:34
		memory) and (438/\$6 257/\$6))) and dual near4 electrode	US-PGPUB;	
		not ((((tft thin near film near transistor) same (capacitor	EPO; JPO;	
		memory) and ((257/59,53,54,57,184,187).CCLS.))) and	DERWENT;	
	1	dual near3 electrode)	I IBM TDB	1